

STPSC2006CW

600 V power Schottky silicon carbide diode

Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- Particularly suitable in PFC boost diode function

Description

The SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 600 V rating. Due to the Schottky construction no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

ST SiC diodes will boost the performance of PFC operations in hard switching conditions.

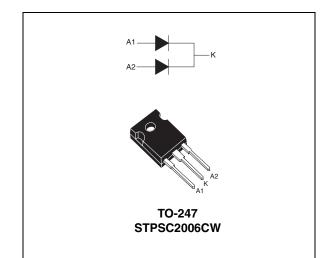


Table 1. Device summary

Symbol	Value
I _{F(AV)}	2 x 10 A
V _{RRM}	600 V
T _{j (max)}	175 °C
Q _{C (typ)}	12 nC

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1 Characteristics

Table 2.Absolute ratings (limiting values at 25 °C unless otherwise specified, per
diode)

Symbol	Para	ameter	Value	Unit
V _{RRM}	Repetitive peak reverse voltage		600	V
I _{F(RMS)}	Forward rms current		18	А
1	Average ferward aurrent	$T_c = 115 \text{ °C}, \delta = 0.5$ Per diode	10	А
I _{F(AV)}	Average forward current	$T_c = 100 \ ^{\circ}C, \ \delta = 0.5$ Per device	20	А
	Surge per repetitive ferward	$t_p = 10 \text{ ms}$ sinusoidal, $T_c = 25 \text{ °C}$	40	
I _{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms sinusoidal}, T_c = 125 ^\circ\text{C}$	32	А
	ourion.	$t_p = 10 \ \mu s \ square, \ T_c = 25 \ ^\circ C$	160	
I _{FRM}	Repetitive peak forward current	40	А	
T _{stg}	Storage temperature range	-55 to +175	°C	
Тj	Maximum operating junction temp	-40 to +175	°C	

Table 3.Thermal resistance

Symbol	Parameter	Value	Unit	
В	Junction to case	Per diode	2	°C/W
R _{th(j-c)}	Sunction to case	Total	1.2	°C/W
R _{th(c)}	Coupling	•	0.4	°C/W

Table 4. Static electrical characteristics per diode

Symbol	Parameter	Tests co	Min.	Тур.	Max.	Unit	
I _B ⁽¹⁾	Reverse leakage	T _j = 25 °C	V _R = V _{RRM}	-	30	150	μA
'R`´	current	T _j = 150 °C	▼R − ▼RRM	-	210	1500	μΑ
V _F ⁽²⁾	Forward voltage drop	T _j = 25 °C	_j = 25 °C I _F = 10 A		1.4	1.7	V
V _F ⁽²⁾ Forward voltage drop		T _j = 150 °C		-	1.6	2.1	v

1. $t_p = 10 \text{ ms}, \delta < 2\%$

2. $t_p = 500 \ \mu s, \ \delta < 2\%$

To evaluate the conduction losses use the following equation: P = 1.2 x $I_{F(AV)}$ + 0.09 x $I_{F}{}^{2}_{(RMS)}$

Table 5.Other parameters per diode

Symbol	Parameter	Test conditions	Тур.	Unit
Q _c	Total capacitive charge	V_r = 400 V, I_F = 10 A dI_F/dt = -200 A/µs T_j = 150 $^\circ C$	12	nC
С	Total capacitance	$V_r = 0$ V, $T_c = 25$ °C, F = 1 Mhz	650	pF



V_R(V)

Figure 1. Forward voltage drop versus forward current

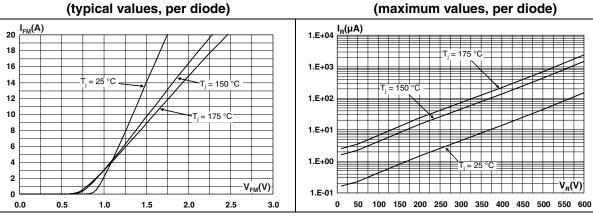


Figure 2.

Figure 3. Peak forward current versus case temperature (per diode)

Figure 4. Junction capacitance versus reverse voltage applied (typical values, per diode)

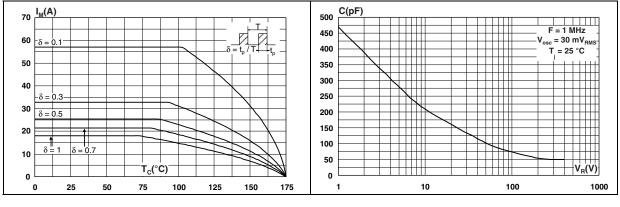
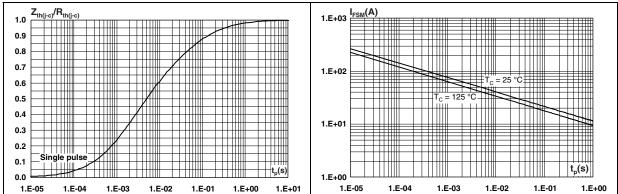


Figure 5. **Relative variation of thermal** impedance junction to case versus pulse duration

Figure 6. Non-repetitive peak surge forward

current versus pulse duration (sinusoidal waveform, per diode)



Reverse leakage current versus

reverse voltage applied

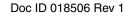


Figure 7.	Total capacitive charge versus dl _F /dt (typical values, per diode)
J · · ·	

	Q _c (nC)									
16	– I _F = 10 A – V _R = 400 V				_					F
14										
12										
				-						+
		\square			_					
8										
6										
4	/				_					
2										
0								dl	/dt(A/	μs)
) 50 1	00 1	50	200	250	300	350	400	450	500



2 Package information

- Epoxy meets UL94, V0
- Cooling method: convection (C)
- Recommended torque value: 0.55 to 1.0 N·m

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Table 6. TO-247 dimensions

		Dimensions				
	Ref.	Millin	neters	Inc	hes	
		Min.	Max.	Min.	Max.	
	Α	4.85	5.16	0.191	0.203	
	D	2.20	2.60	0.086	0.102	
	E	0.40	0.80	0.015	0.031	
	F	1.00	1.40	0.039	0.055	
	F1	3.00) typ.	0.118	3 typ.	
H A	F2	2.00) typ.	0.079	9 typ.	
	F3	1.90	2.40	0.075	0.094	
	F4	3.00	3.40	0.118	0.134	
	G	10.90 typ.		0.429 typ.		
L L2	Н	15.45	16.03	0.608	0.631	
	L	19.85	21.09	0.781	0.830	
$F1 \xrightarrow{F1} F2 \downarrow L1 \xrightarrow{F3} \xrightarrow{F1} F2$	L1	3.70	4.30	0.146	0.169	
$V2$ \downarrow $F4$ D	L2	18.30	19.13	0.720	0.753	
F(x3) M	L3	14.20	20.30	0.559	0.799	
G	L4	34.05	41.38	1.341	1.629	
	L5	5.35	6.30	0.211	0.248	
	М	2.00	3.00	0.079	0.118	
	V	5° .	typ.	5° 1	typ.	
	V2	60°	typ.	60°	typ.	
	Dia.	3.55	3.65	0.140	0.144	



3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode	
STPSC2006CW	STPSC2006CW	TO-247	4.36 g	30	Tube	

4 Revision history

Table 8.Document revision history

Date	Revision	Changes
01-Mar-2011	1	First issue.



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